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Abstract of the Disclosure

An insulating layer which is produced on a semiconductor substrate has a capacitance structure produced in it. The capacitance structure has at least one first substructure which has a metal latticed region and electrically conductive regions which are arranged in the cutouts in the metal latticed region, the metal latticed region are electrically connected to a first connecting line, and the electrically conductive regions are electrically connected to a second connecting line.